

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a wiring comprising tungsten or a tungsten compound including a gate electrode formed over a substrate, the wiring ~~comprising a tungsten nitride film and a tungsten film formed thereon~~ including a gate electrode,

wherein the wiring includes ~~at least one inert element, and 90% or more of the inert element~~ is argon, and

wherein an amount of sodium contained within ~~the tungsten film~~ the wiring is equal to or less than 0.3 ppm.

2. (Currently Amended) The device according to claim 1, wherein ~~a thickness of the tungsten nitride film is 10 to 50 nm and a thickness of the tungsten film is 200 to 400 nm~~ the substrate comprises a glass substrate.

3. (Previously presented) The device according to claim 1, wherein electrical resistivity of the wiring is equal to or less than 40  $\mu\Omega\cdot\text{cm}$ .

4. (Canceled)

5. (Currently Amended) The device according to claim ~~[[4]]~~ 1, ~~further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween~~ wherein

the substrate comprises a silicon substrate.

6-9. (Canceled)

10. (Currently Amended) The device according to claim [[4]] 1, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

11. (Currently Amended) The device according to claim [[4]] 1, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

12. (Currently Amended) The device according to claim [[4]] 1, wherein the wiring is used as a gate electrode of a TFT.

13. (Currently Amended) The device according to claim [[4]] 1, wherein resistance value per 1 square  $\mu$ m of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 $\Omega$ .

14. (Currently Amended) The device according to claim [[4]] 1, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

15. (Currently Amended) The device according to claim [[4]] 1, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital

camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

16-27. (Canceled)

28. (Previously Presented) A semiconductor device comprising:

a wiring formed over a substrate having a lamination structure comprising a phosphorus doped silicon, a nitride film of tungsten, and a film comprising tungsten,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the film comprising tungsten is equal to or less than 0.3 ppm.

29. (Previously presented) The device according to claim 28, wherein the wiring is further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

30. (Previously presented) The device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

31. (Previously presented) The device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

32. (Previously presented) The device according to claim 28, wherein the inert element except for argon is Xe or Kr.

33. (Previously presented) The device according to claim 28, wherein internal stress of the wiring is from  $-1 \times 10^{10}$  dyn/cm<sup>2</sup> to  $+1 \times 10^{10}$  dyn/cm<sup>2</sup>.

34. (Previously presented) The device according to claim 28, wherein line width of the wiring is equal to or less than 5μm.

35. (Previously presented) The device according to claim 28, wherein film thickness of the wiring is equal to or greater than 0.1μm, and equal to or less than 0.7μm.

36. (Previously presented) The device according to claim 28, wherein the wiring is used as a gate electrode of a TFT.

37. (Previously presented) The device according to claim 28, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω.

38. (Previously presented) The device according to claim 28, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

39. (Previously presented) The device according to claim 28, wherein the semiconductor device is an at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

40-63 (Canceled).

64 (New) A semiconductor device comprising:  
a glass substrate;  
a base insulating film comprising silicon nitride or silicon oxynitride over the glass substrate;  
and  
a wiring comprising tungsten or a tungsten compound formed over the base insulating film,  
the wiring including a gate electrode,  
wherein the wiring includes argon, and  
wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

65. (New) The device according to claim 64, wherein the wiring includes at least one of Xe and Kr.

66. (New) The device according to claim 65, wherein an amount of at least one of Xe and Kr included in the wiring is equal to or less than 1 atom%.

67. (New) The device according to claim 65, wherein an amount of at least one of Xe and Kr

included the wiring is equal to or less than 0.1 atom%.

68. (New) The device according to claim 64, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

69. (New) The device according to claim 64, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

70. (New) The device according to claim 64, wherein the wiring is used as a gate electrode of a TFT.

71. (New) The device according to claim 64, wherein resistance value per 1 square  $\mu$ m of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 $\Omega$ .

72. (New) The device according to claim 64, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

73. (New) The device according to claim 64, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

74. (New) A semiconductor device comprising:

a wiring comprising tungsten or a tungsten compound formed over a substrate, the wiring including a gate electrode,

wherein the wiring includes argon,

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm,

and

wherein internal stress of the wiring is from  $-5 \times 10^{10}$  dyn/cm<sup>2</sup> to  $+5 \times 10^{10}$  dyn/cm<sup>2</sup>.

75. (New) The device according to claim 74, wherein the substrate comprises a glass substrate.

76. (New) The device according to claim 74, wherein the substrate comprises a silicon substrate.

77. (New) The device according to claim 74, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

78. (New) The device according to claim 74, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

79. (New) The device according to claim 74, wherein the wiring is used as a gate electrode of a TFT.

80. (New) The device according to claim 74, wherein resistance value per 1 square  $\mu\text{m}$  of surface area of a connection between the wiring and an aluminum wiring is equal to or less than  $40\Omega$ .

81. (New) The device according to claim 74, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

82. (New) The device according to claim 74, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

83. (New) A semiconductor device comprising:

- a glass substrate;
- a base insulating film comprising silicon nitride or silicon oxynitride over the glass substrate;
- and
- a wiring comprising tungsten or a tungsten compound formed over the base insulating film, the wiring including a gate electrode,

wherein the wiring includes argon,

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm,

and

wherein internal stress of the wiring is from  $-5 \times 10^{10} \text{ dyn/cm}^2$  to  $+5 \times 10^{10} \text{ dyn/cm}^2$ .



84. (New) The device according to claim 83, wherein the wiring include at least one of Xe and Kr.

85. (New) The device according to claim 84, wherein an amount of at least one of Xe and Kr included the wiring is equal to or less than 1 atom%.

86. (New) The device according to claim 84, wherein an amount of at least one of Xe and Kr included the wiring is equal to or less than 0.1 atom%.

87. (New) The device according to claim 83, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

88. (New) The device according to claim 83, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

89. (New) The device according to claim 83, wherein the wiring is used as a gate electrode of a TFT.

90. (New) The device according to claim 83, wherein resistance value per 1 square  $\mu$ m of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 $\Omega$ .

91. (New) The device according to claim 83, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL

display, and an active matrix type EC display.

92. (New) The device according to claim 83, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

93. (New) A semiconductor device comprising:

a glass substrate;

a base insulating film comprising silicon nitride or silicon oxynitride formed over the glass substrate;

a wiring comprising tungsten or a tungsten compound formed over the base insulating film, the wiring including a gate electrode, and

an insulating film comprising silicon nitride or silicon oxynitride formed over the wiring,

wherein the wiring includes argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

94. (New) The device according to claim 93, wherein the wiring includes at least one of Xe and Kr.

95. (New) The device according to claim 94, wherein an amount of at least one of Xe and Kr included the wiring is equal to or less than 1 atom%.

96. (New) The device according to claim 94, wherein an amount of at least one of Xe and Kr included the wiring is equal to or less than 0.1 atom%.

97. (New) The device according to claim 93, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

98. (New) The device according to claim 93, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

99. (New) The device according to claim 93, wherein the wiring is used as a gate electrode of a TFT.

100. (New) The device according to claim 93, wherein resistance value per 1 square  $\mu$ m of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 $\Omega$ .

101. (New) The device according to claim 93, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

102. (New) The device according to claim 93, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

103. (New) A semiconductor device comprising:

a wiring comprising tungsten or a tungsten compound formed over a substrate, the wiring including a gate electrode, and

an insulating film comprising silicon nitride or silicon oxynitride formed over the wiring, wherein the wiring includes at least one inert element, and 90% or more of the inert element is argon,

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm, and

wherein internal stress of the wiring is from  $-5 \times 10^{10}$  dyn/cm<sup>2</sup> to  $+5 \times 10^{10}$  dyn/cm<sup>2</sup>.

104. (New) The device according to claim 103, wherein the substrate comprises a glass substrate.

105. (New) The device according to claim 103, wherein the substrate comprises a silicon substrate.

106. (New) The device according to claim 103, wherein the wiring includes at least one of Xe and Kr,

107. (New) The device according to claim 106, wherein an amount of at least one of Xe and Kr included in the wiring is equal to or less than 1 atom%.

108. (New) The device according to claim 106, wherein an amount of at least one of Xe and Kr included in the wiring is equal to or less than 0.1 atom%.

109. (New) The device according to claim 103, wherein line width of the wiring is equal to or less than 5 $\mu$ m.

110. (New) The device according to claim 103, wherein film thickness of the wiring is equal to or greater than 0.1  $\mu$ m, and equal to or less than 0.7 $\mu$ m.

111. (New) The device according to claim 103, wherein the wiring is used as a gate electrode of a TFT.

112. (New) The device according to claim 103, wherein resistance value per 1 square  $\mu$ m of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 $\Omega$ .

113. (New) The device according to claim 103, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

114. (New) The device according to claim 103, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

115. (New) The device according to claim 1, wherein the wiring comprises a tungsten film.

116. (New) The device according to claim 64, wherein the wiring comprises a tungsten film.

117. (New) The device according to claim 74, wherein the wiring comprises a tungsten film.

118. (New) The device according to claim 83, wherein the wiring comprises a tungsten film.

119. (New) The device according to claim 93, wherein the wiring comprises a tungsten film.

120. (New) The device according to claim 103, wherein the wiring comprises a tungsten film.